

ZXMN6A08K

60V DPAK N-channel enhancement mode MOSFET

Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.080 @ $V_{GS}= 10V$	18.2
	0.150 @ $V_{GS}= 4.5V$	13.3



DPAK

Description

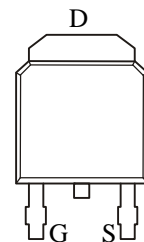
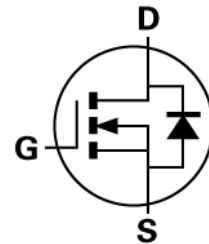
This new generation Trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Features

- Low on-resistance
- Fast switching speed
- Low gate drive
- DPAK package

Applications

- DC-DC Converters
- Power Management functions
- Disconnect switches
- Motor control



Pinout – top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A08KTC	13	16	2,500

Device marking

ZXMN
6A08

Absolute maximum ratings

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current @ $V_{GS}=10V$; $T_C=25^\circ C$ (e) @ $V_{GS}=10V$; $T_C=100^\circ C$ (e)	I_D	18.2 11.5	A
Continuous Drain Current @ $V_{GS}=10V$; $T_A=25^\circ C$ (b) @ $V_{GS}=10V$; $T_A=70^\circ C$ (b) @ $V_{GS}=10V$; $T_A=25^\circ C$ (a)	I_D	8.1 6.5 5.5	A
Pulsed Drain Current (c)	I_{DM}	24.3	A
Continuous Source Current (Body Diode) (b)	I_S	9.0	A
Pulsed Source Current (Body Diode) (c)	I_{SM}	24.3	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	4.1 32.8	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	9.25 74	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (d) Linear Derating Factor	P_D	2.11 16.8	W mW/ $^\circ C$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ C$

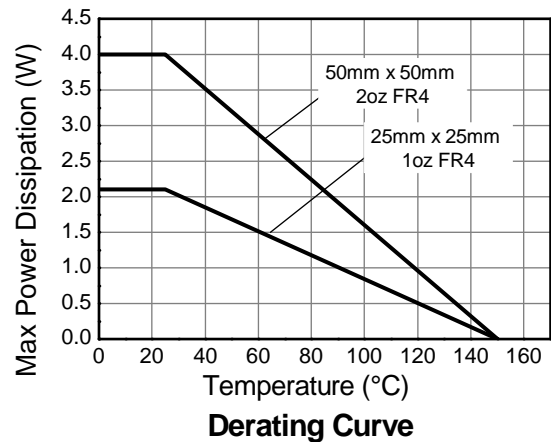
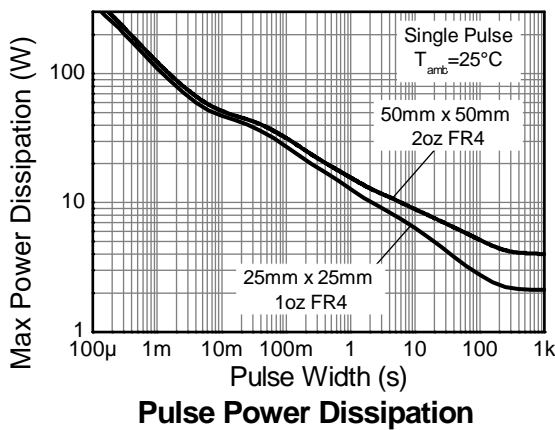
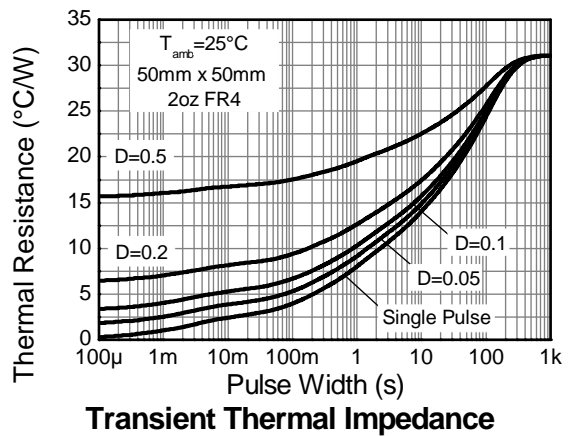
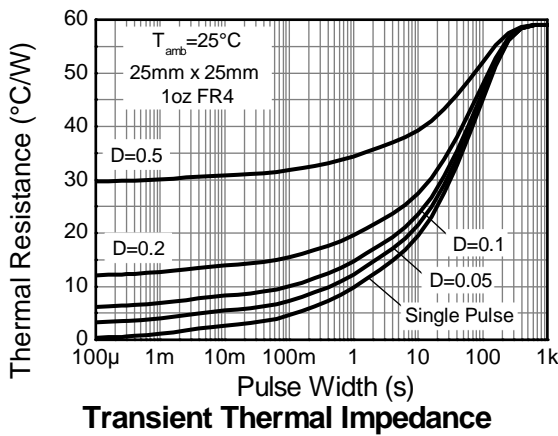
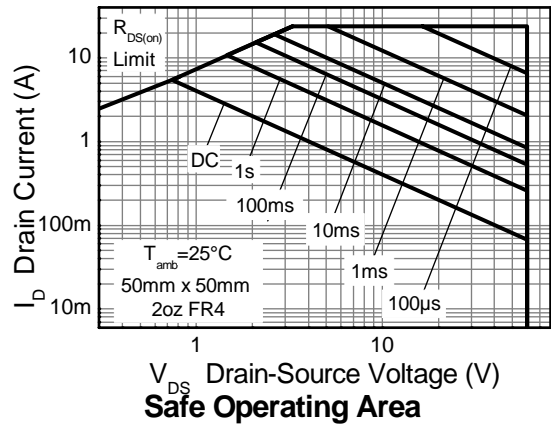
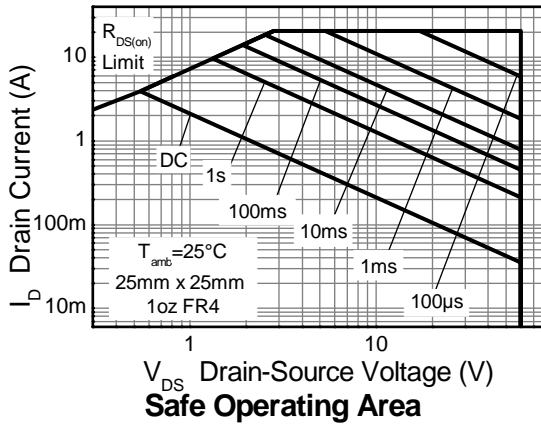
Thermal resistance

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	30.5	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	14.0	$^\circ C/W$
Junction to Ambient (d)	$R_{\theta JA}$	59.1	$^\circ C/W$
Junction to Case (e)	$R_{\theta JC}$	2.77	$^\circ C/W$

NOTES

- For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
- Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, $D=0.02$ pulse width=300 μs – pulse width limited by maximum junction temperature.
- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- The terms case and case temperature refer to the exposed metal back face of the package and the drain pin.

Thermal characteristics



Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

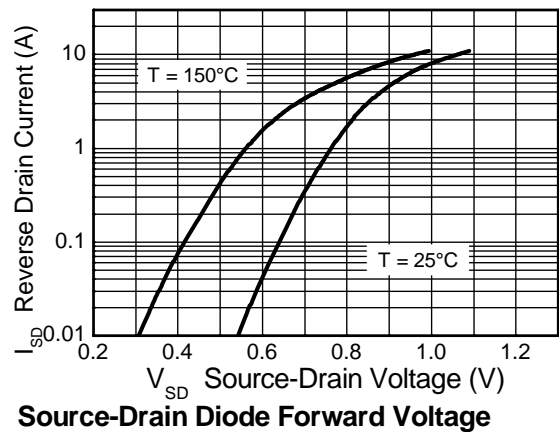
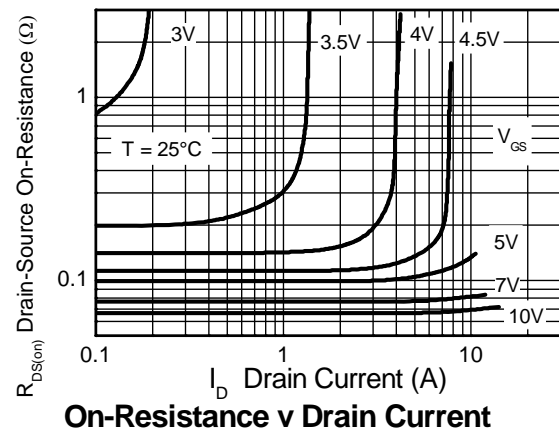
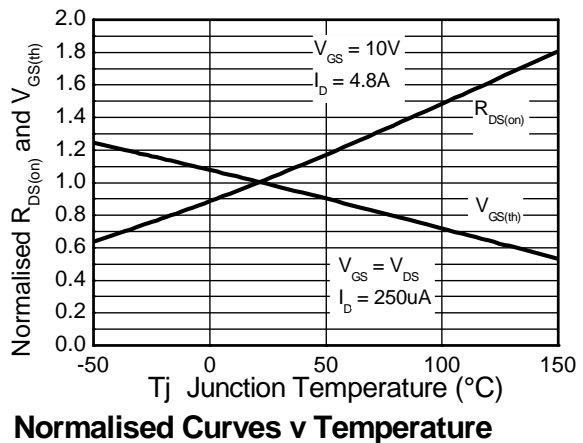
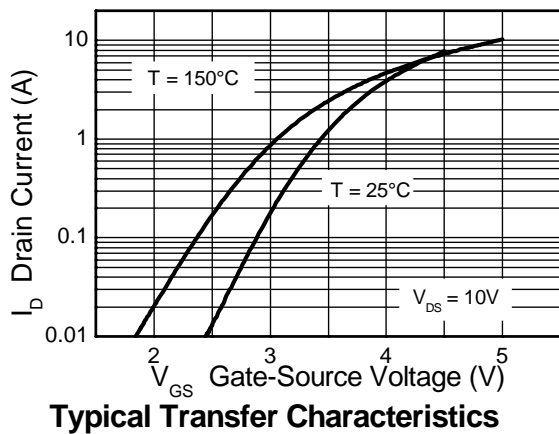
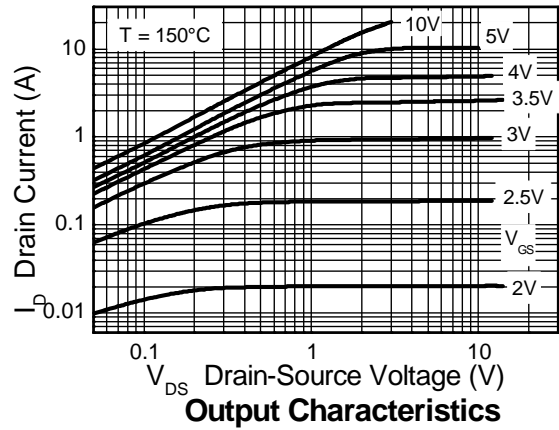
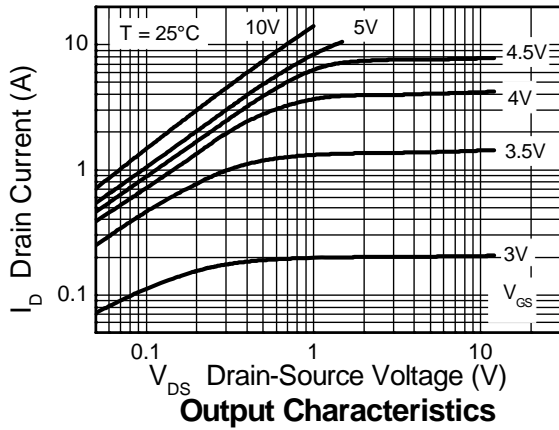
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	60			V	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			0.5	μA	$V_{DS} = 60\text{V}$, $V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1		3	V	$I_D = 250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.080	Ω	$V_{GS} = 10\text{V}$, $I_D = 4.8\text{A}$
				0.150	Ω	$V_{GS} = 4.5\text{V}$, $I_D = 4.2\text{A}$
Forward Transconductance (1) (3)	g_{fs}		6.6		S	$V_{DS} = 15\text{V}$, $I_D = 4.8\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		459		pF	$V_{DS} = 40\text{V}$, $V_{GS} = 0\text{V}$
Output Capacitance	C_{oss}		44.2		pF	$f = 1\text{MHz}$
Reverse Transfer Capacitance	C_{rss}		24.1		pF	
SWITCHING (2) (3)						
Turn-On-Delay Time	$t_{d(on)}$		2.6		ns	$V_{DD} = 30\text{V}$, $I_D = 1.5\text{A}$
Rise Time	t_r		2.1		ns	$R_G = 6.0\Omega$, $V_{GS} = 10\text{V}$
Turn-Off Delay Time	$t_{d(off)}$		12.3		ns	
Fall Time	t_f		4.6		ns	
Gate Charge	Q_g		4.0		nC	$V_{DS} = 30\text{V}$, $V_{GS} = 5\text{V}$ $I_D = 1.4\text{A}$
Total Gate Charge	Q_g		5.8		nC	$V_{DS} = 30\text{V}$, $V_{GS} = 10\text{V}$
Gate-Source Charge	Q_{gs}		1.4		nC	$I_D = 1.4\text{A}$
Gate Drain Charge	Q_{gd}		1.9		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}		0.88	0.95	V	$T_j = 25^{\circ}\text{C}$, $I_S = 4\text{A}$, $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	t_{rr}		19.2		ns	$T_j = 25^{\circ}\text{C}$, $I_S = 1.4\text{A}$,
Reverse Recovery Charge (3)	Q_{rr}		30.3		nC	$di/dt = 100\text{A}/\mu\text{s}$

(1) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

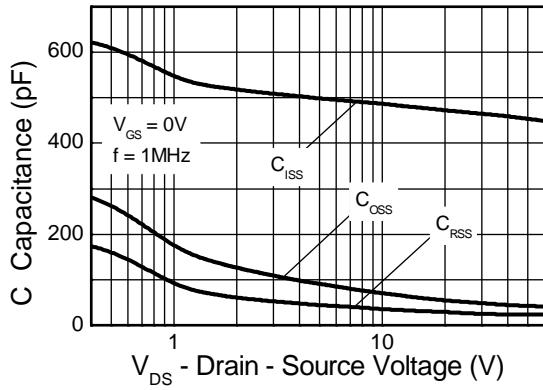
(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

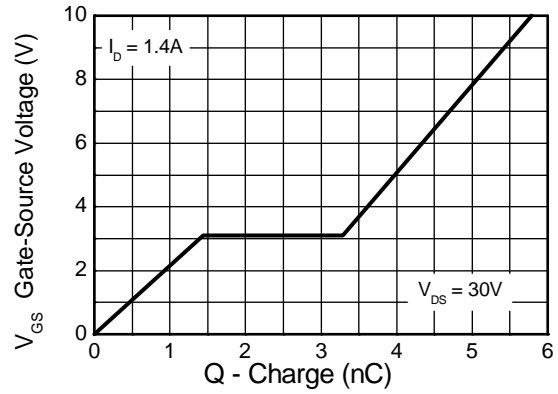
Typical Characteristics



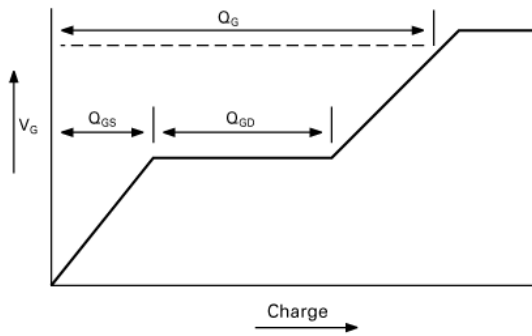
Typical characteristics



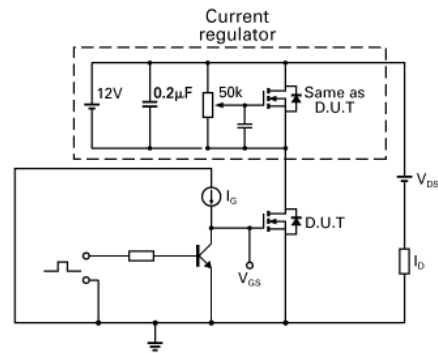
Capacitance v Drain-Source Voltage



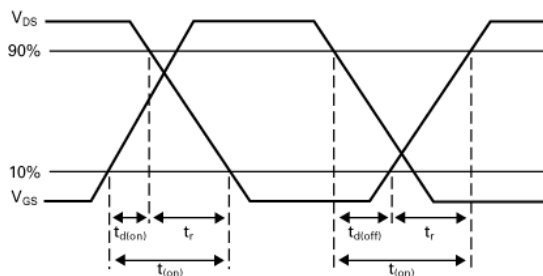
Gate-Source Voltage v Gate Charge



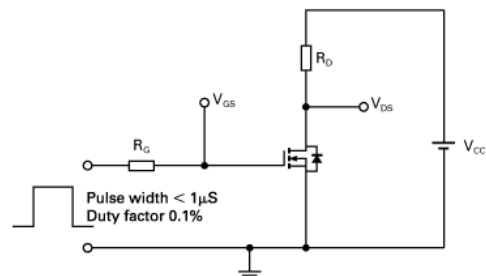
Basic gate charge waveform



Gate charge test circuit



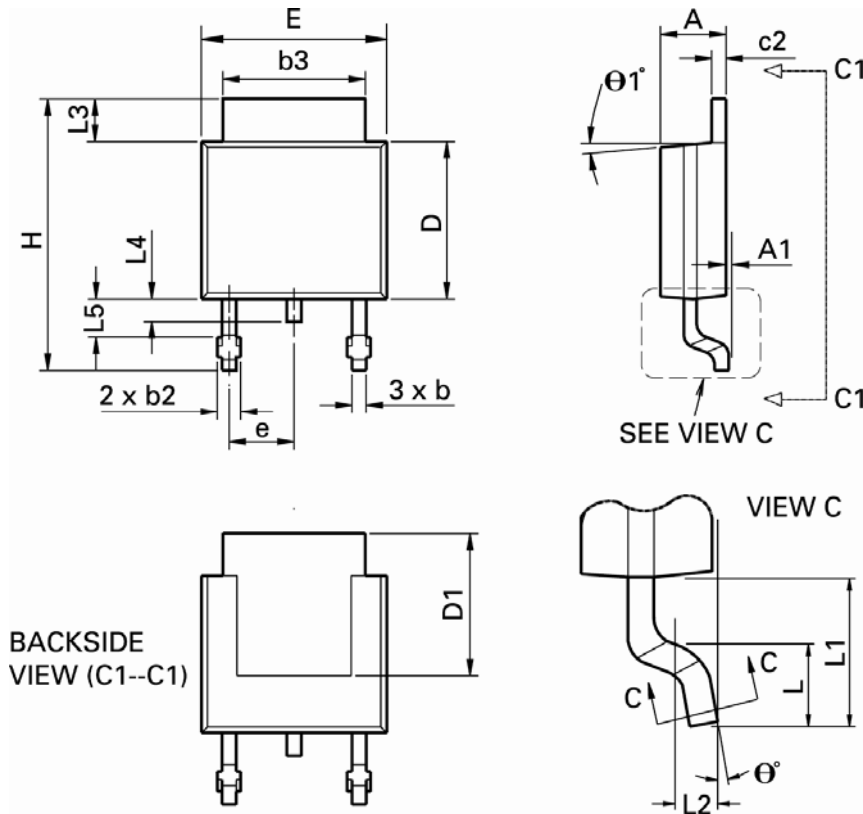
Switching time waveforms



Switching time test circuit

Packaging details – DPAK

Surface mounted, 4 pin package



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	q1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	q°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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"Active"	Product status recommended for new designs
"Last time buy (LTB)"	Device will be discontinued and last time buy period and delivery is in effect
"Not recommended for new designs"	Device is still in production to support existing designs and production
"Obsolete"	Production has been discontinued

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"Provisional version"	This term denotes a pre-release datasheet. It provides a clear indication of anticipated performance. However, changes to the test conditions and specifications may occur, at any time and without notice.
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Sales offices

The Americas

3050 E. Hillcrest Drive
Westlake Village,
CA 91362-3154
Tel: (+1) 805 446 4800
Fax: (+1) 805 446 4850

Europe

Kustermannpark
Balanstraße 59,
D-81541 München
Germany
Tel: (+49) 894 549 490
Fax: (+49) 894 549 4949

Taiwan

7F, No. 50,
Min Chuan Road
Hsin-Tien
Taipei, Taiwan
Tel: (+886) 289 146 000
Fax: (+886) 289 146 639

Shanghai

Rm. 606, No.1158
Changning Road
Shanghai, China
Tel: (+86) 215 241 4882
Fax (+86) 215 241 4891

Shenzhen

Room A1103-04,
ANLIAN Plaza, #4018
Jintian Road
Futian CBD,
Shenzhen, China
Tel: (+86) 755 882 849 88
Fax: (+86) 755 882 849 99

Korea

6 Floor, Changhwa B/D,
1005-5 Yeongtong-dong,
Yeongtong-gu, Suwon-si,
Gyeonggi-do, Korea 443-813
Tel: (+82) 312 731 884
Fax: (+82) 312 731 885